## DESCRIPTION

RT3X99M is composite transistor built with two RTAN230 chips in SC-88 package.

## FEATURE

- Built-in bias resistor ( $\mathrm{R}_{1}=2.2 \mathrm{k} \Omega$ )
- Mini package for easy mounting
- High reverse hFe.
- Small collector to emitter saturation voltage.
$\mathrm{V}_{\mathrm{CE}(\mathrm{sat})}=10 \mathrm{mV}$ (TYP.) $\left(\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA} / \mathrm{I}_{\mathrm{B}}=0.5 \mathrm{~mA}\right)$
- Low on Resistor.
$\mathrm{R}_{\mathrm{ON}}=0.70 \Omega$ (TYP.) $\left(@ \mathrm{~V}_{\mathrm{I}}=5 \mathrm{~V}\right)$


## APPLICATION

Muting circuit, Switching circuit

MAXIMUM RATING $\left(\mathrm{Ta}=25^{\circ} \mathrm{C}\right)(\mathrm{RTr} 1, \mathrm{RTr} 2 \mathrm{COMMON})$

| SYMBOL | PARAMETER | RATING | UNIT |
| :---: | :--- | :---: | :---: |
| VCBO $^{\|c\|}$ | Collector to Base voltage | 40 | V |
| VEBO | Emitter to Base voltage | 40 | V |
| VCEO | Collector to Emitter voltage | 20 | V |
| $\mathrm{IC}_{\mathrm{C}}$ | Collector current | 400 | mA |
| $\mathrm{P}_{\mathrm{T}}$ | Total dissipation | 150 | mW |
| $\mathrm{~T}_{\mathrm{j}}$ | Junction temperature | +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {stg }}$ | Storage temperature | $-55 \sim+150$ | ${ }^{\circ} \mathrm{C}$ |



ELECTRICAL CHARACTERISTICS $\left(\mathrm{Ta}=25^{\circ} \mathrm{C}\right)(\mathrm{RTr} 1, \mathrm{RTr} 2$ COMMON $)$

| SYMBOL | PARAMETER | TEST CONDITIONS | LIMITS |  |  | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | MIN | TYP | MAX |  |
| V(BR)CBO | Collector to Base breakdown voltage | $\mathrm{I}_{\mathrm{C}}=50 \mu \mathrm{~A}, \mathrm{I}_{\mathrm{E}}=0$ | 40 | - | - | V |
| V(BR)EBO | Emitter to Base breakdown voltage | $\mathrm{I}_{\mathrm{E}}=50 \mu \mathrm{~A}, \mathrm{I}_{\mathrm{C}}=0$ | 40 | - | - | V |
| V(BR)CEO | Collector to Emitter breakdown voltage | $\mathrm{I}_{\mathrm{C}}=1 \mathrm{~mA}, \mathrm{R}_{\mathrm{BE}}=\infty$ | 20 | - | - | V |
| ICBO | Collector cut off current | $\mathrm{V}_{\mathrm{CB}}=40 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0$ | - | - | 0.5 | $\mu \mathrm{A}$ |
| IEBO | Emitter cut off current | $\mathrm{V}_{\mathrm{EB}}=40 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=0$ | - | - | 0.5 | $\mu \mathrm{A}$ |
| hFE | DC forward current gain | $\mathrm{V}_{\mathrm{CE}}=5 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}$ | 820 | - | 2500 | - |
| VCE(sat) | Collector to Emitter saturation voltage | $\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=0.5 \mathrm{~mA}$ | - | 10 | - | mV |
| $\mathrm{R}_{1}$ | Input resistor | - | 1.54 | 2.2 | 2.86 | $\mathrm{k} \Omega$ |
| fT | Gain band width product | $\mathrm{V}_{\mathrm{CE}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=-10 \mathrm{~mA}, \mathrm{f}=100 \mathrm{MHz}$ | - | 40 | - | MHz |
| Ron | Output On-resistor | $\mathrm{V}_{\mathrm{I}}=5 \mathrm{~V}, \mathrm{R}_{\mathrm{L}}=1 \mathrm{k} \Omega$ | - | 0.70 | - | $\Omega$ |



## Keep safety first in your circuit designs

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